

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2213612	source\$1drain or s\$1d or drain\$1source or d\$1s	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 11:23
S2	305395	implant\$6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 16:53
S3	5045759	si or silicon or ge or germanium or ar or argon or oxygen or nitrogen or inert or noble or neutral	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 16:55
S4	50487	wet adj5 etch\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 09:22
S5	86956	S2 same S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 16:56
S6	260405	amorpho\$8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 17:04
S7	7214	S5 same S6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 16:58
S8	35059	(trench\$3 or recess\$4) with (S1 or source near2 drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 17:06

S9	236	S7 and S8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 17:01
S10	125	S9 and S4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 17:01
S11	262051	amorph\$9	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 09:31
S12	7625	S2 same S3 same S11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 17:05
S13	52894	(trench\$3 or recess\$4) with etch\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 17:07
S14	451	S12 and S13 and S4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 17:07
S15	3075	aniso\$1tropic\$4 near10 wet near10 etch\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 17:13
S16	34	S12 and S13 and S15	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 17:14

S17	6289	amorph\$9 with implant\$6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 17:28
S18	26	S15 and S17	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 17:40
S19	2774632	trench\$3 or recess\$4 or groov\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 17:41
S20	704	amorph\$9 with (etchstop\$4 or etch\$3 adj3 stop\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 17:42
S21	63	S19 same S20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 18:01
S22	3071	(438/198 or 438/300 or 438/516 or 438/524 or 438/528 or 438/705 or 438/752 or 438/753).ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 09:21
S23	50487	wet adj5 etch\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 09:23
S24	520136	koh or naoh or (sodium or potassium or ammonia) adj3 hydroxide or "nh.sub.4oh" or "nh. sub.4 oh" or tmah or tetra\$1methyl\$1ammonia	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 09:28

S25	562630	S23 or S24	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 09:28
S26	927	S22 and S25	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 09:28
S27	262051	amorph\$9	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 09:31
S28	256	S26 and S27	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 09:32
S29	2213612	source\$1drain or s\$1d or drain\$1source or d\$1s	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 11:26
S30	36	(epitax\$4 or epi) with (fill\$4 or re\$1fill\$4 or backfill\$4 or back adj3 fill\$4) with (si or silicon or ge or germanium or semiconduct\$3) with S29	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 11:38
S31	46478	(fill\$4 or re\$1fill\$4 or backfill\$4 or back adj3 fill\$4) with (S29 or drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 11:34
S32	14894	equivalen\$2 with (plane or orientation)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 12:08

S33	1442833	crystal\$8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 11:48
S34	3603	S32 and S33	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 11:41
S35	14799837	"100" or "001"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 12:02
S36	2721	S34 and S35	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 11:42
S37	686	S32 same S35 and S33	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 11:49
S38	1096150	crystal or crystalograph\$7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 11:49
S39	660	S32 same S35 and S38	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 11:50
S40	3911047	semiconductor or si or silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 12:57

S41	518	S39 and S40	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 11:51
S42	15947618	"100" or "001" "010" or "111" or "110" or "011" or "101"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 12:05
S43	6358017	plane or orientation or direction	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 12:24
S44	934933	(S29 or source or drain) same S42	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 12:38
S45	520501	(trench\$2 or groove or recess\$4 or cavity) same S42	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 12:22
S46	513355	(S44 or S45) and S40	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 12:27
S47	49545	S46 and S43 and (S38 or crytal\$8)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 12:31
S48	377661	S42 with S43	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 12:35

S49	15854	S47 and S48	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 12:35
S50	241314	(S29 or source or drain) same S42 same S43	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 12:49
S51	195192	S45 same S43	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 12:48
S52	1012224	gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 12:50
S53	214988	(S50 and S52) or S51	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 12:51
S54	10312	S53 and S38 and S40	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 12:52
S55	4502	S54 and (S25 or S27)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 12:53
S56	780948	S40 near7 device	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 12:59

S57	2757	S55 and S56	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 12:59
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